Abstract

A method is proposed for etching patterns in an etching body (18), in particular cut-outs in a silicon body (18) exactly defined in a lateral manner, using a plasma (14). In this context, a high-frequency-pulsed high-frequency power is at least temporarily coupled into the etching body (18) via an at least temporarily applied high-frequency a.c. voltage. This coupled, high-frequency-pulsed high-frequency power is further modulated at a low frequency, in particular clocked. The proposed method opens a wide process window for varying the etching parameters in the implemented plasma etching process, and is especially suitable for etching patterns in silicon using high mask selectivity and high etching rates for simultaneously minimized charge effects, in particular with respect to notching on the dielectric boundary surface.

(Figure 1)